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2. (Amended) The dielectric substrates, as recited in claim 1, further comprising:
said dielectric substrates being heated for at least 20 hours at between 1400° C and 1600 °

5 C;

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said dielectric substrates having a low dielectric constant in the range of 4.1 to 16.3; and
said dielectric substrates having a low dielectric loss in the range of less than 1×10^{-3} to 9×10^{-3} without a phase transition.

10 4. (Twice Amended) The dielectric substrate, according to claim 3, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite cubic crystalline structure;
said dielectric substrate having a low dielectric constant of 15.1; and
said dielectric substrate having a low dielectric loss of less than 1×10^{-3} .

15 *B2*
7. (Twice Amended) The dielectric substrate, according to claim 6, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;
20 said dielectric substrate having a low dielectric constant of 5.1; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

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25 10. (Twice Amended) The dielectric substrate, according to claim 9, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline
structure;
said dielectric substrate having a low dielectric constant of 10.0; and
said dielectric substrate having a low dielectric loss of 2.0×10^{-3} .

30 *B4*
13. (Twice Amended) The dielectric substrate, according to claim 12, further comprising:

BS
said dielectric substrate is constructed in a bulk form;

5 said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;

10 said dielectric substrate having a low dielectric constant of 5.3; and

15 said dielectric substrate having a low dielectric loss of 1.6×10^{-3} .

16. (Twice Amended) The dielectric substrate, according to claim 15, further comprising:

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said dielectric substrate is constructed in a bulk form;

20 said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;

25 said dielectric substrate having a low dielectric constant of 11.6; and

30 said dielectric substrate having a low dielectric loss of about 3.1×10^{-3} .

19. (Twice Amended) The dielectric substrate, according to claim 18, further comprising:

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said dielectric substrate is constructed in a bulk form;

20 said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;

25 said dielectric substrate having a low dielectric constant of 11.2; and

30 said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

22. (Twice Amended) The dielectric substrate, according to claim 21, further comprising:

BS
said dielectric substrate is constructed in a bulk form;

25 said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline structure;

30 said dielectric substrate having a low dielectric constant of 12.9; and

35 said dielectric substrate having a low dielectric loss of 1.4×10^{-3} .

BG
25. (Twice Amended) The dielectric substrate, according to claim 24, further comprising:

30 said dielectric substrate is constructed in a bulk form;

35 said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline

structure;

B6
said dielectric substrate having a low dielectric constant of 7.1; and

said dielectric substrate having a low dielectric loss of 1.4×10^{-3} .

5 28. (Twice Amended) The dielectric substrate, according to claim 27, further comprising:

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said dielectric substrate is constructed in a bulk form;

said dielectric substrate having an ordered perovskite cubic crystalline structure;

said dielectric substrate having a low dielectric constant of 16.3; and

said dielectric substrate having a low dielectric loss of 3.8×10^{-3} .

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31. (Twice Amended) The dielectric substrate, according to claim 30, further comprising:

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said dielectric substrate is constructed in a bulk form;

said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline

structure;

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said dielectric substrate having a low dielectric constant of 12.1; and

said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

34. (Twice Amended) The dielectric substrate, according to claim 33, further comprising:

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said dielectric substrate is constructed in a bulk form;

said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline

structure;

said dielectric substrate having a low dielectric constant of 13.6; and

said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

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37. (Twice Amended) The dielectric substrate, according to claim 36, further comprising:

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said dielectric substrate is constructed in a bulk form;

said dielectric substrate having an ordered perovskite pseudo-cubic tetragonal crystalline

structure;

said dielectric substrate having a low dielectric constant of 10.9; and

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said dielectric substrate having a low dielectric loss of 2.2×10^{-3} .